ALPHA & OMEGA SEMICONDUCTOR

AO4830L
Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO4830L uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge . This device is suitable for use as a load switch or in PWM applications.

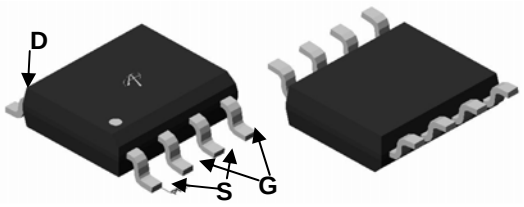
- RoHS Compliant
- Halogen Free

Features

V_{DS} (V) = 80V
I_D = 3.5A (V_{GS} = 10V)
$R_{DS(ON)}$ < 75mΩ (V_{GS} = 10V)

100% UIS Tested!
100% R_g Tested!

SOIC-8



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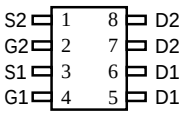

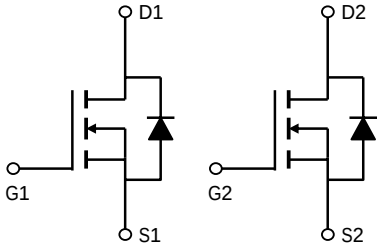

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	T_A=25°C	I_D	3.5	A
	T_A=70°C		2.9	
Pulsed Drain Current [C]		I_{DM}	18	
Avalanche Current [C]		I_{AR}	16	A
Repetitive avalanche energy L=0.1mH [C]		E_{AR}	12.8	mJ
Power Dissipation [B]	T_A=25°C	P_D	2	W
	T_A=70°C		1.3	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	48	62.5	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		74	90	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	32	40	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	80			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±30V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	3.5	4.2	5	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	18			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=3.5A		62	75	mΩ
		T_J=125°C		113.0	135	
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=3.5A		15		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.77	1	V
I_S	Maximum Body-Diode Continuous Current				2.5	A
I_{SM}	Pulsed Body-diode Current[C]				18	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=40V, f=1MHz	510	640	770	pF
C_{oss}	Output Capacitance		28	40	52	pF
C_{rss}	Reverse Transfer Capacitance		12	20	30	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.9	1.8	2.7	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=40V, I_D=3.5A	8	11	13	nC
Q_g(4.5V)	Total Gate Charge		4	5.5	7	
Q_{gs}	Gate Source Charge		4	5	6	nC
Q_{gd}	Gate Drain Charge		0.7	1.2	1.7	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=40V, R_L=8Ω, R_{GEN}=3Ω		7.2		ns
t_r	Turn-On Rise Time			2.2		ns
$t_{D(off)}$	Turn-Off DelayTime			17		ns
t_f	Turn-Off Fall Time			2		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=3.5A, dI/dt=300A/µs	14	20	26	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=3.5A, dI/dt=300A/µs	35	50	65	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initialT_J=25°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in ^{2} FR-4 board with

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

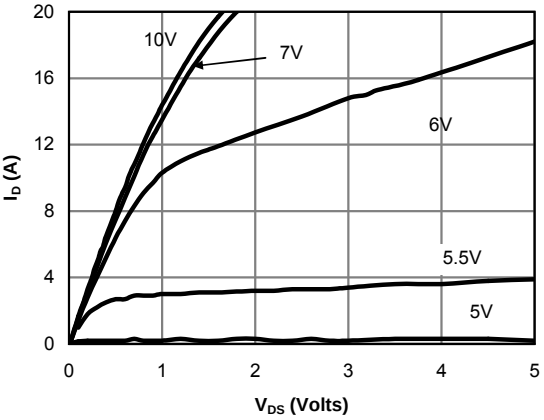


Fig 1: On-Region Characteristics (Note E)

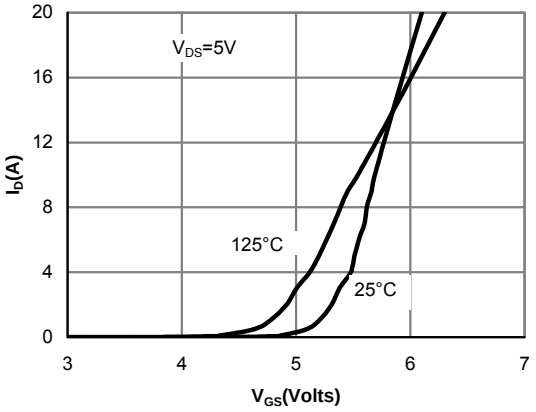


Figure 2: Transfer Characteristics (Note E)

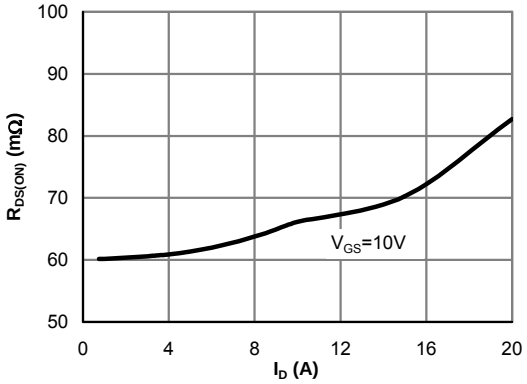


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

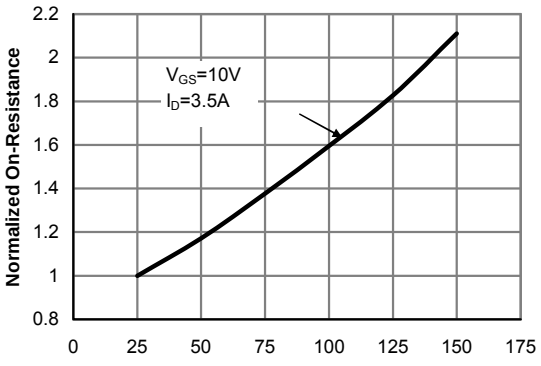


Figure 4: On-Resistance vs. Junction Temperature (Note E)

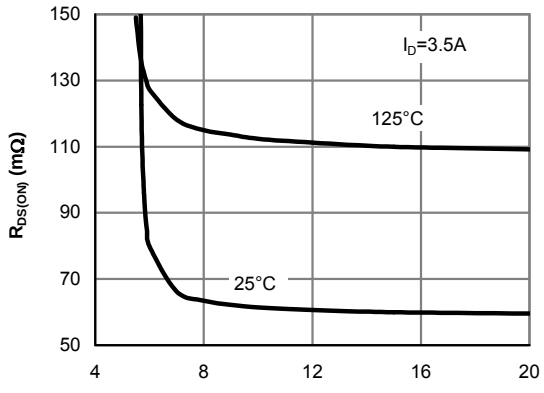


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

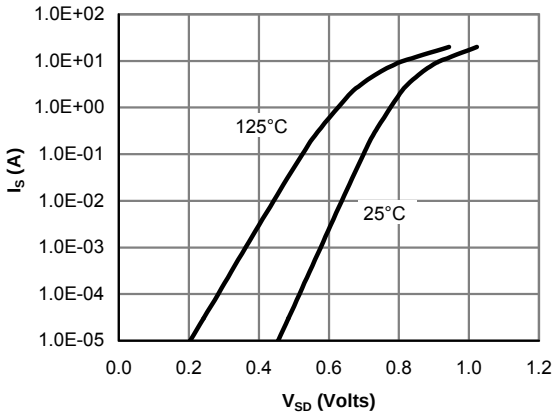


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

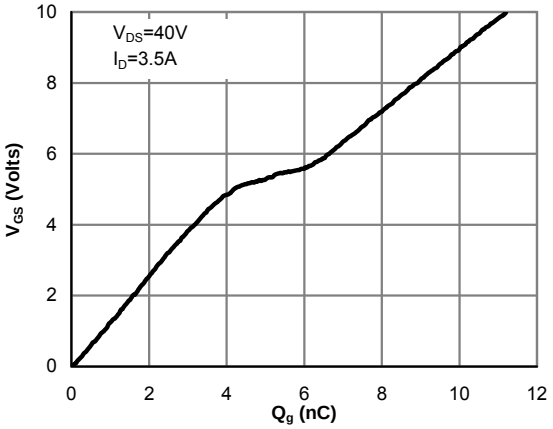


Figure 7: Gate-Charge Characteristics

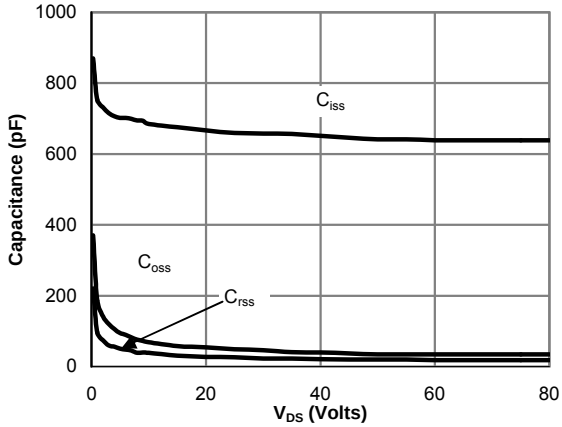


Figure 8: Capacitance Characteristics

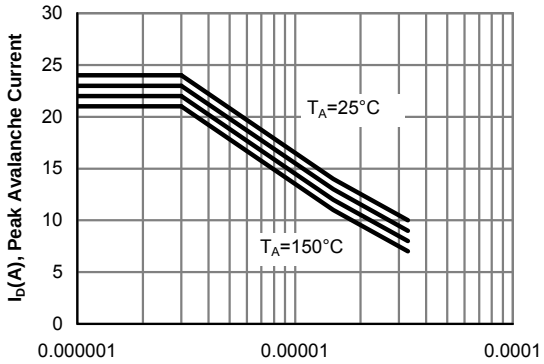


Figure 12: Single Pulse Avalanche capability

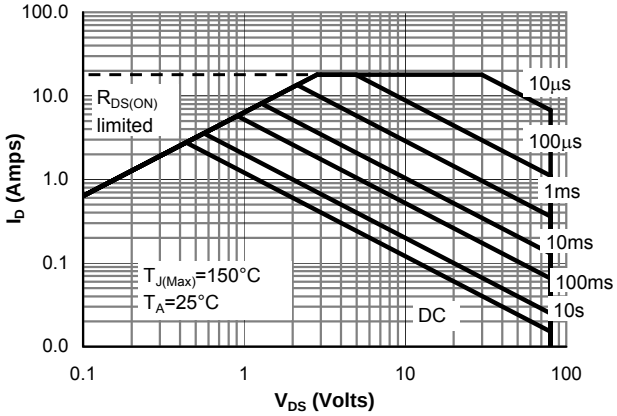


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

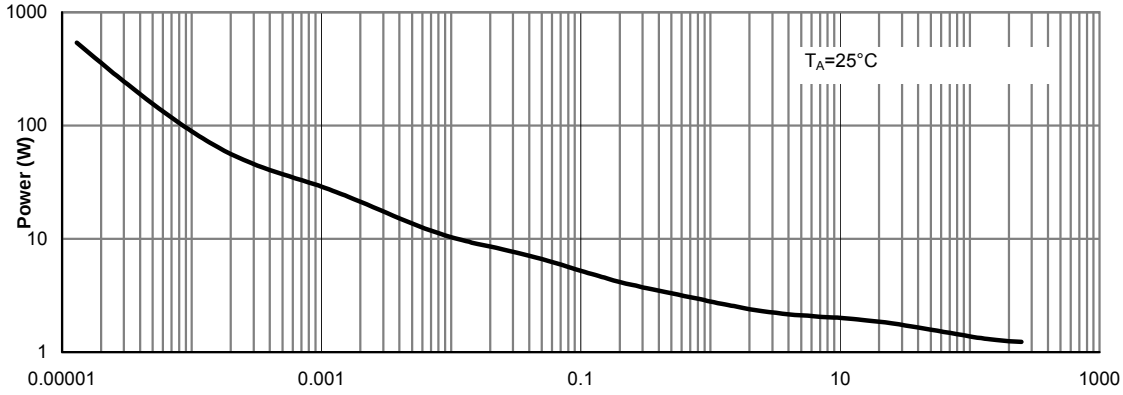


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

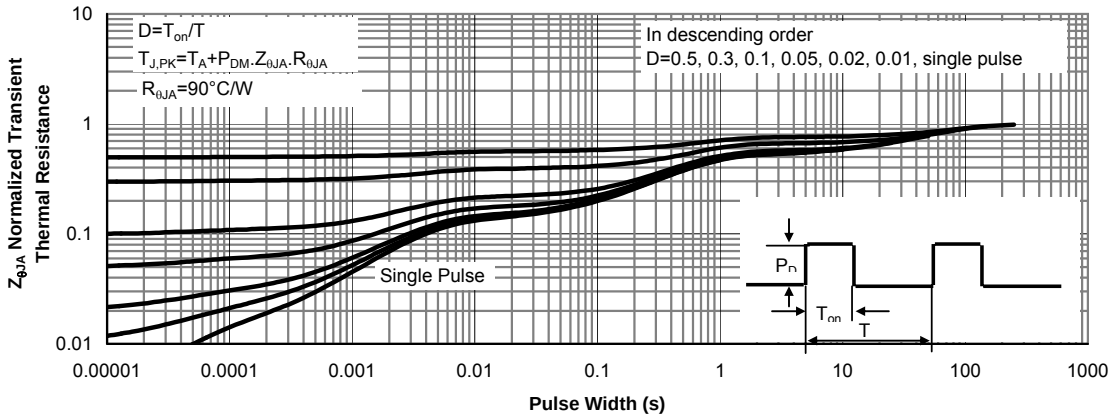
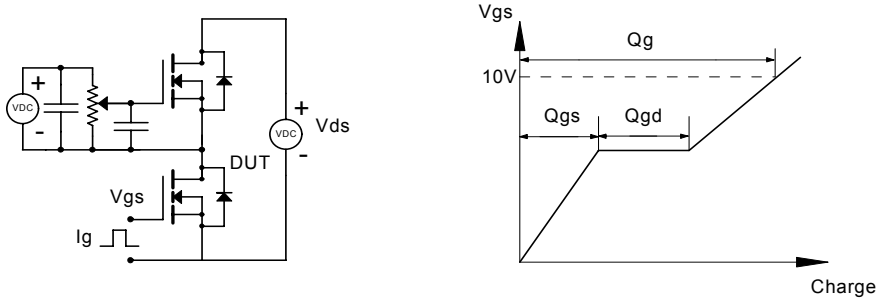
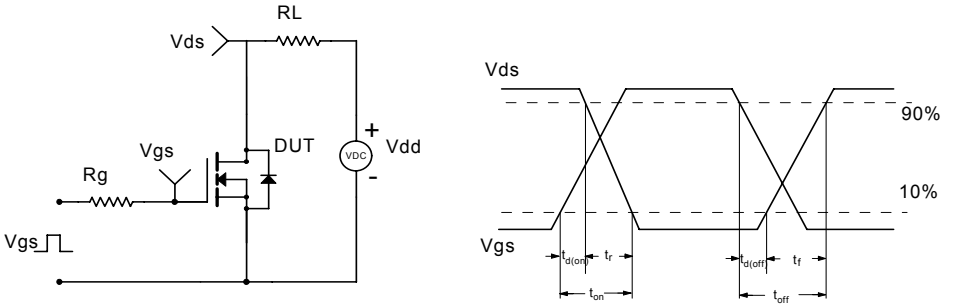


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

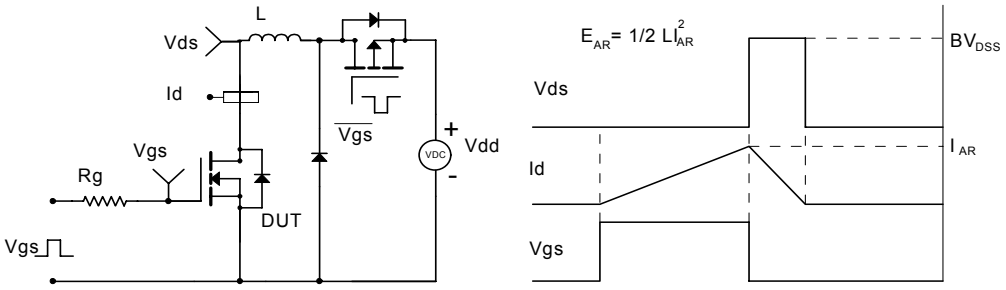
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms